

Area Selective ALD

Room Event Hall - Session AS-TuP

Area Selective ALD Poster Session

AS-TuP-1 Advancing AS-ALD of WSe₂ Through Nature-Inspired Engineering, *Kylee Lamberson, Chih-hung Chang*, Oregon State University

Area-selective atomic layer deposition (AS-ALD) of WSe₂ offers significant promise for advancing electronic and energy technologies. Our research introduces an innovative approach that combines microreactor-assisted nanomaterial deposition (MAND) with nature-inspired chemical engineering (NICE) to achieve safe, efficient, and lithography-free deposition with enhanced temporal resolution of nanomaterials like WSe₂. Drawing inspiration from the ovipositor mechanism of the parasitic wasp *Diachasmimorpha longicaudata*, we developed a bio-inspired seed pretreatment strategy to optimize substrate surface preparation. This method utilizes a deposition nozzle to locate the seed material precisely, mimicking the wasp's ability to find a host organism for egg deposition. In our MAND system, selenium is generated in situ via a reaction between solid selenium powder and forming gas, eliminating the need for hazardous bulk storage of H₂Se. Tungsten is introduced through pulsed heating of solid W(CO)₆, generating tungsten carbonyl molecules. Then, alternating flows of W(CO)₆, inert gas, and H₂Se facilitate the selective deposition of WSe₂ onto micro- and nanoscale seeds. Seed shape and chemical properties were optimized using insights from literature and density functional theory (DFT) simulations. By varying source transport rates, we studied the nucleation and growth of WSe₂, enabling detailed analysis of growth kinetics and process optimization. Advanced characterization techniques, including scanning electron microscopy (SEM), atomic force microscopy (AFM), Fourier-transform infrared spectroscopy (FTIR), and X-ray photoelectron spectroscopy (XPS), were employed to validate and refine the process. This work highlights the transformative potential of integrating NICE and MAND for scalable, safe, and efficient AS-ALD of WSe₂, paving the way for innovative advancements in semiconductor manufacturing and energy technologies.

AS-TuP-2 Advancements in Area-Selective Deposition by Merck: From Fundamental Principles to Industrial Applications, *Isiah Liu*, Merck KGaA, Darmstadt, Taiwan; *Lanxia Cheng, Tingmin Wang, Matthew MacDonald, Bhushan Zope*, Merck KGaA, Darmstadt; *Chang-won Lee*, Merck KGaA, Darmstadt, Korea (Democratic People's Republic of); *Masashi Jinguji, Xinjian Lei*, Merck KGaA, Darmstadt

Area Selective Deposition (ASD) processes have gained significant attention due to the limitations of current lithographic techniques in fabricating advanced semiconductor devices, particularly as device dimensions continue to shrink. For the development of future semiconductor nodes, a critical process is required to selectively grow thin films on specific surfaces while preventing deposition on others. This process must effectively differentiate between surfaces to ensure precise material deposition. To address these challenges, Merck has developed systematic concepts based on the surface reactions involved in selective deposition, which require a comprehensive understanding of surface chemistry and the reactivity of inhibitors to passivate non-growth areas. The inhibitor layer plays a crucial role in the ASD process by acting as a protective barrier, selectively preventing deposition on undesired regions of the substrate while ensuring material growth occurs only on the targeted surfaces. These surface reactions were initially explored through molecular modeling and subsequently confirmed through application tests and in-situ metrologies. Through extensive studies, the optimal selection of inhibitors, coupled with the development of the ASD process, has been successfully achieved, enabling precise control over material deposition in advanced semiconductor fabrication. This progress has led to the development of several novel ASD processes that have attracted significant interest within the industry, demonstrating the ability to selectively passivate dielectric (SiO₂, Si₃N₄, Si) and metal (Cu) substrates. This breakthrough offers a promising solution for the precise control of material deposition, representing a critical advancement for the fabrication of next-generation semiconductor devices.

AS-TuP-3 Comparative Study of Experimental and DFT Calculations of Trimethylaluminum Adsorption on SiO₂, SiN, and Si for Area-Selective Deposition, *Genki Hayashi, Ni Zeyuan, Yumiko Kawano, Shinichi Ike, Shuji Azumo*, Tokyo Electron Technology Solutions Limited, Japan

Area-Selective Deposition (ASD) is an attractive process for semiconductor manufacturing[1]. It utilizes the differences of the surface chemical reaction between a precursor molecule and different substrates. Surface reaction simulations are useful tools for screening appropriate ASD precursors[2]. In this study, we investigated the validity of adsorption energy calculation using density functional theory (DFT) by comparing the calculation with the process outcomes.

We calculated the adsorption energy of Trimethylaluminum (TMA) molecule on H-terminated Si, OH-terminated SiO₂, and NH-, OH- and F-terminated SiN substrates (Fig1(a)). Here, TMA is a well-known precursor that is often used for Al₂O₃ deposition, and the choices of these surface terminations were based on the usual dilute HF (DHF) treatment prior to precursor introduction to remove native oxides[3]. It is widely known that H (OH) terminated surface was formed for Si (SiO₂) surface after DHF. For SiN surface, it was found from X-ray photoelectron spectroscopy (XPS) measurement (Fig1(b)) that fluorine was clearly detected on the surface, suggesting that not only OH and NH but also non-negligible amount of F was terminated on the surface, which is consistent with the previous study [3]. The calculated adsorption energy (Fig1(a)) was lower in order of the SiO₂(-OH), SiN(-OH), SiN(-NH), Si(-H), and SiN(-F) cases. This suggested that TMA is most likely to adsorb on the SiO₂(-OH) surface, whereas most unlikely to adsorb on SiN(-F) surface.

To compare the simulation results with experiments, we actually introduced TMA to Si, SiO₂, and SiN substrates in a chamber after DHF. Fig1(c) shows the XPS results (Al 2p) of these substrates after TMA flow. The largest amount of Al (resulting from TMA adsorption) was observed on the SiO₂ substrate, which agrees with the speculation from the simulation results. For SiN substrate, we also performed H₂O dipping treatment for 12.5 h at maximum after DHF, and consecutively, TMA flow experiment. As shown in Fig2(a) (XPS results), amount of fluorine decreased for 12.5-h H₂O dipping, suggesting that -F is replaced by -OH. Corresponding to this, it was found from XPS measurement (Fig2(b)) that amount of Al increased. This experimental result is consistent with the adsorption energy calculation (Fig1(a)) where TMA is more likely to adsorb on SiN(-OH) than on SiN(-F). These results demonstrate the usefulness of the DFT calculations to estimate selectivity in developing ASD.

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AS-TuP-4 An Automated Adsorption Simulation Workflow for Efficient High-Throughput Molecule Screening for Area-Selective Deposition, *Zeyuan Ni, Michitaka Aita*, Tokyo Electron Technology Solutions Ltd., Japan; *Ayuta Suzuki*, TEL Technology Center, America, LLC; *Genki Hayashi, Yumiko Kawano, Shinichi Ike, Shuji Azumo*, Tokyo Electron Technology Solutions Ltd., Japan

Area-selective deposition (ASD), a “chemical patterning” method that can reduce the fabrication cost and achieve novel structures beyond lithography, is gathering increasing global interests from researchers in semiconducting industry.¹⁻³ One of the key items to realize ASD on two specific types of areas is the selection of reactants and/or inhibitors from over thousands of candidate molecules. Compared to experiments, the first-principles simulation is a more accessible approach with lower cost and higher speed. Yet, a thorough simulation for an adsorption event requires searching for several most energetically favorable saddle points (i.e. transition states) in the potential energy surface, which makes it demanding in computation resources for high-throughput exploration.

In this work, we developed a simple surrogate automatic simulation workflow for evaluation of a molecule's adsorption behavior on surfaces by using density functional theory (DFT) software VASP and automation packages fireworks and atomate⁴. First, we performed manual simulations of the adsorption behavior for N-(Trimethylsilyl)dimethylamine (TMSDMA) C₅H₁₅NSi on 7 types of surfaces by using the NEB method. It is found that the activation energy E_a is almost in proportion to the adsorption energy after molecule dissociation, which is denoted as E_{d,ads}. (Fig. 1) Such empirical relationship is similar to the well-known Bell-Evans-Polanyi principle⁵, so we believe E_{d,ads} can serve as a reasonable surrogate metric for E_a.

Accordingly, an automatic $E_{d,ads}$ simulation workflow that can break molecules into fragments and search for the most stable adsorption configuration automatically has been implemented (Fig. 2) and tested for 4 types of molecules on Ru and hydroxyl-terminated SiO₂ (SiO₂-OH) surface. For each molecule-substrate pair, multiple adsorption configurations have been investigated, from which the most stable one is chosen to represent the final adsorption energy of the molecule on the specific surface (Fig. 3). Within the 4 molecules we investigated, we find that the difference of alkynes' adsorption energies on Ru and SiO₂-OH is the largest, outperforming TMSDMA, carboxylic acids, and pyridine. Alkynes could be promising inhibitors blocking Ru surface compared to SiO₂-OH.

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AS-TuP-5 Self-Assembled Inhibitor for Area-Selective Deposition on Cu Interconnects to Lower Contact Resistance, *Yun Ki Kim*, Samsung Electronics, Republic of Korea; *Sang Chul Youn*, Samsung Electronics Co., Republic of Korea

Beyond the 5nm node, the limitations in producing nanostructures for chip production have necessitated the adoption of new materials for Cu interconnects, as the existing Ta/TaN systems have structural limitations and performance issues that hinder their effectiveness. To overcome these challenges, area-selective atomic layer deposition (ALD) techniques are employed, wherein self-assembled monolayers (SAMs) are utilized to deactivate ALD growth on pre-patterned surfaces. In this study, SAM inhibitors were used to selectively block TaN layer formation on Cu interconnects, resulting in a significant reduction in contact resistance by approximately 63%. This reduction is primarily attributed to the prevention of direct TaN deposition on Cu, with a selectivity ratio of 2.85. Furthermore, the optimal thickness for both the SAM and TaN layers was determined to be 200 °C. At last, the long-term stability in a wide range of temperature (-20–60 °C) for 18 months was investigated, and verified the suitability for mass production chips.

AS-TuP-6 Optimization of Small Molecular Inhibitors for Area-Selective Atomic Layer Deposition by Controlling Alkyl Chain Length, *EunChong Cho*, Korea Research Institute of Chemical Technology (KRICT), Republic of Korea; *Hae Lin Yang*, Hanyang University, Korea; *Jung-Hoon Lee*, Korea Research Institute of Chemical Technology (KRICT), Republic of Korea; *Jin-Seong Park*, Hanyang University, Korea; *Youngkwon Kim*, Korea Research Institute of Chemical Technology (KRICT), Republic of Korea

This study addresses the limitations of conventional self-assembled monolayers (SAMs) in area-selective atomic layer deposition (AS-ALD) by investigating small molecular inhibitors (SMIs) for vapor-phase deposition. SMIs were designed based on trimethoxyphenylsilane (TMPS) with varying alkyl chain lengths ($n = 1-6$) interposed between the phenyl and silicon. The SMIs were characterized using nuclear magnetic resonance (NMR) spectroscopy and evaluated for passivation effectiveness through water contact angle (WCA) measurements on SiO₂ substrates and AS-ALD experiments. The WCA of SMIs with shorter alkyl chains ($n = 1-3$) was higher than TMPS, while those of SMIs with longer chains ($n = 4-6$) were lower. To evaluate the selectivity of SMIs in AS-ALD experiments, we first deposited SMI on SiO₂ and TiN substrates, followed by VO₂ deposition. SiO₂ was used as a non-growth area, while TiN served as a growth area. As a result, the shorter chain SMIs ($n = 1-3$) achieved over 85% selective inhibition efficiency on SiO₂ relative to TiN, in contrast to TMPS showing ~67% efficiency. The optimal selective inhibition efficiency of about 90% was observed for $n = 2$. In contrast, longer chain SMIs ($n = 4-6$) exhibited diminishing selective inhibition efficiency, correlated well with WCA results. This study provides valuable insights for future SMI designs in AS-ALD applications, contributing to the advancement of nanoscale semiconductor fabrication techniques.

AS-TuP-7 Area-Selective Atomic Layer Deposition of Amino Silane-Based Small Molecule Inhibitor for Enhancement of Selectivity, *Jae Hun Hwang*, *EunChong Cho*, *Youngkwon Kim*, Korea Research Institute of Chemical Technology (KRICT), Republic of Korea

Area-selective atomic layer deposition (AS-ALD) is one of the next-generation technologies that enable bottom-up fabrication, in contrast to the traditional top-down fabrication used in semiconductor manufacturing.

AS-ALD has the potential to reduce the number of lithographic patterning steps considerably. Furthermore, AS-ALD enables angstrom-level accuracy in specific regions of substrates with diverse chemical properties when fabricating thin film devices. In this study, we applied small molecular inhibitors (SMIs) in AS-ALD to address the issues of low volatility and uniformity in gas-phase processes of conventional self-assembled monolayers (SAMs). We compared two SMIs, trimethoxyphenylsilane (TMPS) and tri(dimethylamino)phenylsilane (TDMAPS), containing methoxides and dimethylamines as the head groups that can interact with the substrates.

The synthesized SMIs were characterized using nuclear magnetic resonance spectroscopy. SMIs were deposited using ALD, and water contact angle measurements were performed on four substrates (SiO₂, SiN, TiN, and Cu) to evaluate the coverage and passivation effectiveness. After depositing a Ru film on the SMIs-coated substrate using the Ru precursor [Ru(II)(η^5 -C₇H₇O)(η^5 -C₇H₉)], the film thickness was measured via X-ray fluorescence analysis. X-ray photoelectron spectroscopy was performed to conduct a precise elemental analysis of Ru. TDMAPS deposited on SiO₂ and SiN substrates showed 100% selectivity for 150 cycles of Ru deposition, while deposition occurred on Cu and TiN substrates after a slight nucleation delay, confirming the substrate-specific chemo-selectivity. In particular, the TDMAPS-coated SiO₂ and SiN showed higher selectivity of Ru precursors compared to those of TMPS, which is attributed to the of higher reaction rates amino groups with the substrate. This study demonstrates the importance of the head groups of SMIs to enhance the selectivity in AS-ALD and provides guidelines for the design of SMIs.

AS-TuP-8 Substrate-Driven Selectivity in Area-Selective Atomic Layer Deposition of ZnO: A Theoretical Investigation, *Semin Kim*, *Yeseul Son*, *Taeyoung Kim*, *Soo-Hyun Kim*, *Byungjo Kim*, UNIST, Republic of Korea

As semiconductor devices continue to scale down while demanding higher performance, precise process control and a fundamental understanding of atomic-scale surface reactions become essential. Area-Selective Atomic Layer Deposition (ASALD) has emerged as a promising technique, enabling material growth in designated regions by leveraging surface chemical properties. Unlike conventional ALD, ASALD eliminates the need for additional patterning steps, inherently achieving selective deposition at the nanoscale. This makes ASALD particularly relevant for next-generation semiconductor devices, where precise material placement is critical, such as in 3D-integrated circuits and functional thin-film applications.

Zinc oxide (ZnO), a transparent conductive oxide, has garnered significant interest due to its excellent electrical and optical properties. It is widely used in next-generation semiconductor devices, transparent electrodes, optoelectronic components, and gas sensors. While previous studies on ZnO ASALD have primarily focused on inhibitor-based selective deposition, the influence of inherent substrate properties on ZnO film growth and incubation cycles remains largely unexplored.

In this study, Density Functional Theory (DFT) and molecular dynamics (MD) simulations were conducted to examine how different substrate compositions (SiO₂, Ti, Cu, and Ru) influence ZnO ALD precursor adsorption. To better capture realistic surface configurations, a machine learning force field (MLFF) was implemented, enabling MD simulations that more accurately reflect atomic interactions. Additionally, extensive DFT calculations were performed to quantify the intricate interactions occurring at different surfaces. The analysis revealed substantial variations in precursor-surface interactions, including significant differences in adsorption energies during physisorption. Furthermore, discrepancies in ligand exchange reaction energies were observed, leading to notable shifts in ZnO growth kinetics depending on the substrate. These differences directly impacted incubation cycles, providing a theoretical foundation for substrate-driven selectivity in ZnO ASALD.

By leveraging these insights, we establish a theoretical framework for understanding how chemical reactants interact with different surfaces and how substrate characteristics can be intentionally modified to induce inherent selectivity. This work highlights the importance of a strong theoretical foundation in optimizing atomic layer processing for unprecedented selectivity, offering a pathway to precise pattern control in advanced semiconductor manufacturing.

AS-TuP-9 Inherent Area-Selective Atomic Layer Deposition of Molybdenum Carbide for Bottom-up Semiconductor Manufacturing

Jeong Hwan Han, Min Seok Kim, Ji Sang Ahn, Seoul National University of Science and Technology, Republic of Korea

With the increasing demand for higher integration and enhanced performance in semiconductor devices, area-selective atomic layer deposition (AS-ALD) is playing a crucial role. AS-ALD is a technology that can precisely deposit nanometer-level thin films in desired areas, effectively addressing issues that may arise during unnecessary pattern formation or processing. Particularly, selective deposition of metal materials in metallization, and further advanced packaging, where multiple layers of metal need to be deposited sequentially, has the advantage of implementing more complicated structures. Molybdenum carbide (MoC_x) is gaining attention as a promising material for the next generation semiconductor manufacturing due to its excellent mechanical and electrical properties as well as high thermal and chemical stability, there are few reports on Mo-based materials for AS-ALD.

In this study, we developed molybdenum carbide (MoC_x) thermal ALD using a novel combination of Mo precursor and co-reactant, and conducted analysis of the film properties. Notably, it was observed that the film growth behavior varied depending on the substrates by analyzing Mo areal density and film thickness. MoC_x films growth was effectively suppressed on Al_2O_3 substrate, whereas significant film deposition was observed on Cu substrate. Despite being a dielectric substrate, the SiO_2 substrate showed similar growth behavior to Cu, suggesting these processes preferred to suppress MoC_x deposition on Al_2O_3 . The MoC_x process achieved ~ 10.4 nm selective deposition on Cu over Al_2O_3 (94.2 % selectivity) and ~ 13.9 nm on SiO_2 over Al_2O_3 (92.8 % selectivity). These findings demonstrate the feasibility of selective deposition on different substrates, particularly with Al_2O_3 as non-growth area (NGA). This study aims to present an effective approach to overcome technical limitations in next-generation device manufacturing by proposing a method for ASD not only in metal-dielectric applications but also between dielectrics through their inherent AS-ALD process of molybdenum carbide.

Acknowledgements

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AS-TuP-10 Photo-Assisted Atomic Layer Deposition of Metallic Nickel

Yup Tang, Ion Lambrou, Ville Jokinen, Ville Mikkulainen, Aalto University, Finland

Photo-assisted atomic layer deposition (Photo-ALD) provides a fundamentally new approach for inherently selective thin film growth, leveraging photo-induced activation rather than traditional surface activation or deactivation methods. In this work, we demonstrate that Ni Photo-ALD achieves selective deposition on a broad range of semiconducting metal oxide substrates, while completely suppressing growth on insulating surfaces—a improvement over previously reported Cu-based processes, which were limited to grow on fewer substrates. The unique optical and chemical interaction between photo, the precursor, and the semiconducting surfaces allows for selective activation, enabling Ni selective growth without the need for external inhibitors or complex patterning steps. This work not only demonstrates the versatility of Ni Photo-ALD across diverse oxide substrates but also highlights its potential as a scalable technique for selective material growth in advanced fabrication processes.

AS-TuP-11 Logic Applications of Area Selective Deposition beyond 1.4nm

Hoon Seok Seo, Kang Sub Yim, Samsung Electronics, Republic of Korea

The scaling of semiconductor devices has significantly increased transistor density, which has improved the performance of various electrical devices ranging from computers to smartphones. Through such an evolutionary miniaturization, a semiconductor manufacturing technology has required more fine deposition and patterning techniques. However, in the existing nano-fabrication processes based on lithography, it is highly challenging to form an accurate pattern alignment and limited to handle interfacial phenomena inside device. Accordingly, the semiconductor industry has intensively focused on 'area selective deposition (ASD)'. It provides a powerful technique to yield area-selective interfaces of metal/low-k material by using the self-aligned molecules as an inhibitor. In this article, we discussed the application of ASD into logic products. In particular, we introduced the evaluation results for the reverse selective barrier metal

(RSBM) and fully aligned via (FAV) that are being applicable to the backend of line (BEOL).

AS-TuP-12 Impurity-Free Accelerators in Atomic Layer Deposition: Driving the Growth of Low-Resistivity Ultrathin Iridium Films

Se-Hun Kwon, Myung-Jin Jung, Pusan National University, Republic of Korea

Iridium (Ir) has a low figure of merit ($\rho_0 \times \lambda$) and a high melting temperature, so it has recently been spotlighted as a very important copper (Cu) alternative interconnect material in next-generation semiconductor devices. In particular, atomic layer deposition (ALD) enables the deposition of ultra-thin, conformal, and uniform films with excellent step coverage, even in highly complex or narrow trench structures of several-nm dimensions, due to its inherent self-limiting characteristic. In this regard, ALD-Ir is considered one of the most suitable metallization processes for advanced semiconductor interconnect applications.

To develop a reliable ALD-Ir process with improved film quality, considerable efforts have been made. Recently, an ALD-Ir process exhibiting low electrical resistivity and negligible oxygen impurities was reported using Tricarbonyl (1,2,3- η)-1,2,3-tri(tert-butyl)-cyclopropenyl iridium ($\text{C}_{18}\text{H}_{27}\text{IrO}_3$ or TICP) precursor and oxygen [1]. However, despite these advantages, this TICP precursor exhibits a long incubation period and high nucleation delay, making it difficult to deposit extremely thin and continuous Ir films on the hydroxyl-terminated oxide surface.

Therefore, in this study, a method for depositing highly uniform and continuous ALD-Ir thin films with low resistivity even on oxide materials was explored by significantly reducing the incubation period and promoting nucleation through impurity-free accelerators under simple process conditions. This additional step does not change the existing device structure while enabling the formation of high-quality Ir thin films with strong resistance to external impurities. Furthermore, we systematically compared and analyzed the nucleation and growth behavior, as well as film properties, of ALD-Ir on the oxide surface under process conditions with and without the accelerator. As a result, we successfully obtained ultrathin ALD-Ir films with superior uniformity, low surface roughness, and low resistivity, even on oxide surfaces.

References

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AS-TuP-13 Area-Selective Atomic Layer Deposition of High-K Dielectric Oxides on Self-Assembled Monolayer Functionalized Nitride Substrates

Ting-I Wu, Shih-Hao Tseng, Department of Materials Science and Engineering, National Yang Ming Chiao Tung University, Hsinchu, Taiwan; *Thanh Danh La Duc*, Department of Materials Science and Engineering, National Yang Ming Chiao Tung University, Hsinchu, Viet Nam; *Yu-Chuan Lin, Hong-Cheu Lin, Yung-Jung Hsu*, Department of Materials Science and Engineering, National Yang Ming Chiao Tung University, Hsinchu, Taiwan

As semiconductor devices shrink, advanced bottom-up manufacturing techniques are required to fabricate nano-scale electronic devices efficiently. To prevent the misalignment encountered in conventional patterning, area-selective atomic layer deposition (AS-ALD) could serve as a promising solution in the semiconductor industry. In this work, we discuss the utility of self-assembled monolayers (SAMs) on nitride substrates, such as SiN or TiN. Benzaldehydes and their functionally derivative groups were used to explore the blocking effects of SAMs utilizing their chemically inert functional groups and carbon chains in various length. Through a variety of surface measurements including water contact angle (WCA), Fourier-transform Infrared spectroscopy (FTIR), x-ray photoelectron spectroscopy (XPS), scanning probe microscopy (SPM), we verified bonding, coverage, and uniformity of our chosen SAMs on nitrides. Next, SAM-coated nitrides will be used as the substrates to grow AlO_x films via ALD to investigate the blocking effect of the chosen SAMs and correlate their ALD selectivity with SAM thermal stability and SAM surface coverage on nitrides. These results could help advance the manufacturing and scaling of next generation nanoelectronics.

AS-TuP-14 Stabilization of Metal Coated Silicon Photocathodes for Light Assisted CO₂ Conversion by Area Selective-Atomic Layer Deposition

Encarnacion Torralba Penalver, Harsh Chaliyawala, Nikola Ilic, CNRS-ICMPE, France; *Damien Coutancier*, CNRS-IPVF, France; *Stephane Bastide, Kadiatou Bah, Christine Cachet-Vivier*, CNRS-ICMPE, France; *Negar Naghavi, Nathanaelle Schneider*, CNRS-IPVF, France

Photoelectrochemical CO₂ reduction (PEC-CO₂RR) is a promising approach for producing sustainable fuels and chemicals. While many semiconductors have been investigated, silicon-based electrodes modified with metal

nanoparticles (NPs) remain underutilized, despite their potential for scalable and cost-effective applications. Among metal catalysts, **copper (Cu) NPs** are widely studied for their ability to generate hydrocarbons and oxygenates. However, their **instability** under reaction conditions—including aggregation, detachment, and dissolution—leads to loss of activity and altered selectivity. These issues are exacerbated under PEC-CO₂RR conditions due to combined light-induced and electrochemical stress, as well as the low catalyst loadings required for efficient light absorption.

Alloying Cu with other metals like Ag or Pd can improve stability, though the effect depends on alloy composition, synthesis, and operating conditions. We recently demonstrated that **Metal-Assisted Chemical Etching (MACE)** is an effective and low-cost method for depositing **bimetallic NPs** (e.g., AgCu, PdCu) on p-Si supports, yielding promising performance in terms of current density and selectivity. However, **Cu-rich systems still degrade rapidly**, highlighting the need for additional stabilization strategies such as **protective coatings or nanostructuring**.

In this work, we investigate a novel stabilization method using **Area-Selective Atomic Layer Deposition (AS-ALD)** to coat silicon-based photocathodes with functional oxide layers. AS-ALD leverages the **chemical reactivity contrast** between SiO₂ and metal surfaces, enabling selective deposition of Al₂O₃ onto the silicon substrate while leaving metal NP surfaces largely uncovered. By tuning precursor chemistry, deposition temperature, and cycle number, we developed **nanometer-thick Al₂O₃ coatings** that protect the substrate without blocking catalytic sites.

Initial PEC-CO₂RR tests of protected electrodes (Ag, Cu, and AgCu NPs on p-Si) show **enhanced NP stability** and **reduced hydrogen evolution**, likely due to decreased exposure of bare Si to the electrolyte. Characterization via XPS, SEM, and PEC measurements confirms partial preservation of the catalyst structure. Some degradation still occurs, likely due to Al₂O₃ porosity. Ongoing work focuses on improving the robustness of the ALD coatings to further enhance long-term durability.

AS-TuP-15 Molecular Design of ALD Precursors Through Atomic-Level Simulation and Their Reactivity Analysis, *Yusuke Asano, Kota Matsumoto, Makoto Sato*, Preferred Computational Chemistry, Japan

Atomic Layer Deposition (ALD) is a process that forms uniform thin films with atomic-level precision. Within this process, Area-Selective Deposition (ASD)—a technique that achieves film growth selectively on specific areas—has garnered significant attention, and recent research has been actively focused on it. With advancements in computational chemistry, the atomic-level mechanisms in ALD processes have been elucidated, enabling the design of ALD processes and ALD precursors using these insights.

In this study, we propose a method for designing ASD-suitable precursor molecules using atomic-level simulations with an universal machine learning interatomic potential (uMLIP). Specifically, we constructed an adsorption energy dataset for various precursor model molecules using adsorption energy calculations for areas where film formation is desired and areas where it is not (modeled as H-terminated Si surfaces and alkyl-protected surfaces, respectively). Through the sparse modeling of this data, we extracted ligand features that enhance adsorption selectivity towards H-terminated Si surfaces and alkyl-protected surfaces. Consequently, we successfully identified ligand candidates that increase adsorption selectivity towards H-terminated Si surfaces.

Furthermore, by combining a uMLIP with the Global Reaction Route Mapping (GRRM) method, we successfully analyzed the ligand dissociation mechanisms of ALD precursor molecules on surfaces. These methods allow for the design of precursor molecules that meet the high adsorption selectivity and ligand dissociation requirements necessary for ASD.

AS-TuP-16 Photocatalytic Surface Initiation for Area-Selective Deposition of Polymer Thin Films and Sustainable Nanomanufacturing, *Yuanhao Shen, Xinlei He, Xiaocheng Huang, Pengzhe Cai, Delong Liu, Junjie Zhao*, Zhejiang University, China

Non-lithographic patterning of polymer thin films enables facile fabrication of nanostructures and devices for applications spanning from soft electronics to biomedical engineering. Developing area-selective deposition (ASD) for polymers could achieve self-aligned polymer growth, fostering the generation of complex structures and device configurations with enhanced precision and versatility. However, due to the rapid radical propagation in chain reactions, achieving area-selective radical polymerization in all-dry processes still represents a huge challenge. For conventional initiated chemical vapor deposition (iCVD) and photo-initiated chemical vapor deposition (PiCVD), free radicals are primarily generated in the vapor

phase, which leads to uniform deposition with negligible selectivity on different surfaces.

Here, we report a photocatalytic strategy to achieve surface-specific radical generation for polymer ASD. Because radicals are generated by the reaction between photogenerated holes and monomers, photocatalytic surface-initiated chemical vapor deposition (PS-iCVD) not only eliminates the need for initiator, but also can localize radical generation on the photoactive surfaces, which enables ASD of polymer thin films. Moreover, for semiconductors with narrow bandgaps, such as native oxide of Fe, the PS-iCVD can also enable polymer ASD under visible light for fabricating self-aligned patterns with high area-selectivity (97.4% at deposition thicknesses more than 40 nm). The PS-iCVD offers placement control over chain-growth polymers, providing insights for guiding the design of eco-friendly deposition methods and bottom-up non-lithographic nanofabrication. These polymer patterns shown in this work are expected to serve as inhibitors and templates for achieving area-selective atomic layer deposition.

AS-TuP-17 Atomistic Modeling of Selective SiO₂ Deposition: Inhibiting Si₃N₄ with Benzaldehyde, *Seungwon Shim, Byung Chan Lee, Youngho Kang*, Incheon National University, Republic of Korea; *Soo-Hyun Kim*, Ulsan National Institute of Science and Technology, Republic of Korea; *Han-Boram Lee*, Incheon National University, Republic of Korea

Area-selective atomic layer deposition (AS-ALD) has emerged as a crucial technique for fabricating semiconductor devices, addressing the limitations of conventional top-down patterning methods based on photolithography. In particular, AS-ALD of SiO₂ on SiO₂ surfaces over SiO₂/Si₃N₄ patterns is considered essential for manufacturing charge trap layers (CTLs) in highly scaled 3D NAND devices with high aspect ratios and reduced ONO tier dimensions. Among various approaches to SiO₂ AS-ALD, the use of small-molecule inhibitors (SMIs) to passivate Si₃N₄ surfaces shows significant promise due to its effectiveness and minimal side effects. For successful implementation of SMI-based AS-ALD, a thorough understanding of the physical and chemical processes involved during film deposition is critical.

In this study, we theoretically investigate SiO₂ AS-ALD on a SiO₂/Si₃N₄ pattern using benzaldehyde (BAD) as a SMI, using density functional theory (DFT) calculations. We first examine the adsorption behavior of BAD on both Si₃N₄ and SiO₂ surfaces to confirm its preferential binding to Si₃N₄. Next, we analyze the reaction between BAD adsorbed on Si₃N₄ and ozone (O₃), a commonly used oxidant in ALD processes, to understand how BAD loses its blocking functionality under oxidative conditions. We also study the potential for BAD re-adsorption on Si₃N₄ following oxidation, evaluating whether repeated inhibitor dosing restores its blocking capability during AS-ALD cycles.

Our DFT results show that BAD selectively adsorbs onto Si₃N₄ surfaces, effectively inhibiting precursor deposition. However, exposure to ozone degrades BAD, resulting in a loss of its blocking performance. Notably, the blocking property is recoverable through repeated BAD dosing, provided the Si₃N₄ surface is only partially oxidized. Once the surface becomes fully oxidized and terminated with –OH groups, re-adsorption becomes significantly hindered.

Overall, our findings demonstrate that BAD serves as a promising inhibitor for SiO₂ AS-ALD due to its selective adsorption on Si₃N₄. Although ozone exposure degrades BAD, its blocking function is restorable through timely re-dosing. These results highlight the importance of controlling re-exposure timing in cyclic AS-ALD processes to maintain selective deposition.

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— A —

Ahn, Ji Sang: AS-TuP-9, 3
Aita, Michitaka: AS-TuP-4, 1
Asano, Yusuke: AS-TuP-15, **4**
Azumo, Shuji: AS-TuP-3, 1; AS-TuP-4, 1

— B —

Bah, Kadiatou: AS-TuP-14, 3
Bastide, Stephane: AS-TuP-14, 3

— C —

Cachet-Vivier, Christine: AS-TuP-14, 3
Cai, Pengzhe: AS-TuP-16, 4
Chaliyawala, Harsh: AS-TuP-14, 3
Chang, Chih-hung: AS-TuP-1, 1
Cheng, Lanxia: AS-TuP-2, 1
Cho, EunChong: AS-TuP-6, **2**; AS-TuP-7, 2
Coutancier, Damien: AS-TuP-14, 3

— D —

Danh La Duc, Thanh: AS-TuP-13, 3

— H —

Han, Jeong Hwan: AS-TuP-9, 3
Hayashi, Genki: AS-TuP-3, **1**; AS-TuP-4, 1
He, Xinlei: AS-TuP-16, 4
Hsu, Yung-Jung: AS-TuP-13, 3
Huang, Xiaocheng: AS-TuP-16, 4
Hwang, Jae Hun: AS-TuP-7, **2**

— I —

Ike, Shinichi: AS-TuP-3, 1; AS-TuP-4, 1
Ilic, Nikola: AS-TuP-14, 3

— J —

Jinguji, Masashi: AS-TuP-2, 1

Jokinen, Ville: AS-TuP-10, 3

Jung, Myung-Jin: AS-TuP-12, **3**

— K —

Kang, Youngho: AS-TuP-17, 4
Kawano, Yumiko: AS-TuP-3, 1; AS-TuP-4, 1
Kim, Byungjo: AS-TuP-8, 2
Kim, Min Seok: AS-TuP-9, **3**
Kim, Semin: AS-TuP-8, **2**
Kim, Soo-Hyun: AS-TuP-17, 4; AS-TuP-8, 2
Kim, Taeyoung: AS-TuP-8, 2
Kim, Youngkwon: AS-TuP-6, 2; AS-TuP-7, 2
Kim, Yun Ki: AS-TuP-5, **2**
Kwon, Se-Hun: AS-TuP-12, 3

— L —

Lamberson, Kylee: AS-TuP-1, **1**
Lambrou, Ion: AS-TuP-10, 3
Lee, Byung Chan: AS-TuP-17, 4
Lee, Chang-won: AS-TuP-2, 1
Lee, Han-Bo-Ram: AS-TuP-17, 4
Lee, Jung-Hoon: AS-TuP-6, 2
Lei, Xinjian: AS-TuP-2, 1
Lin, Hong-Cheu: AS-TuP-13, 3
Lin, Yu-Chuan: AS-TuP-13, 3
Liu, Delong: AS-TuP-16, 4
Liu, Isiah: AS-TuP-2, **1**

— M —

MacDonald, Matthew: AS-TuP-2, 1
Matsumoto, Kota: AS-TuP-15, 4
Miikkulainen, Ville: AS-TuP-10, 3

— N —

Naghavi, Negar: AS-TuP-14, 3
Ni, Zeyuan: AS-TuP-4, **1**

— P —

Park, Jin-Seong: AS-TuP-6, 2

— S —

Sato, Makoto: AS-TuP-15, 4
Schneider, Nathanaelle: AS-TuP-14, **3**
Seo, Hoon Seok: AS-TuP-11, **3**
Shen, Yuanhao: AS-TuP-16, **4**
Shim, Seungwon: AS-TuP-17, **4**
Son, Yeseul: AS-TuP-8, 2
Suzki, Ayuta: AS-TuP-4, 1

— T —

Tang, Yupu: AS-TuP-10, **3**
Torralba Penalver, Encarnacion: AS-TuP-14, 3
Tseng, Shih-Hao: AS-TuP-13, 3

— W —

Wang, Tingmin: AS-TuP-2, 1
Wu, Ting-I: AS-TuP-13, **3**

— Y —

Yang, Hae Lin: AS-TuP-6, 2
Yim, Kang Sub: AS-TuP-11, 3
Youn, Sang Chul: AS-TuP-5, 2

— Z —

Zeyuan, Ni: AS-TuP-3, 1
Zhao, Junjie: AS-TuP-16, 4
Zope, Bhushan: AS-TuP-2, 1